## MOSFET - N-Channel, SOT-23

300 mA, 20 V

These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### **Features**

- Low R<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature SOT–23 Surface Mount Package Saves Board Space
- MVMBF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable\*
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	20	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	± 20	Vdc
Drain Current - Continuous @ $T_A$ = 25°C - Continuous @ $T_A$ = 70°C - Pulsed Drain Current ( $t_p \le 10 \mu s$ )	I <sub>D</sub> I <sub>D</sub> I <sub>DM</sub>	300 240 750	mAdc
Total Power Dissipation @ T <sub>A</sub> = 25°C	$P_{D}$	225	mW
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	TL	260	ç

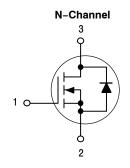
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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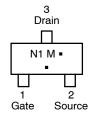
## 300 mAMPS – 20 VOLTS $R_{DS(on)} = 1 \Omega$



## MARKING DIAGRAM AND PIN ASSIGNMENT



SOT-23 CASE 318 STYLE 21



N1 = Specific Device Code
M = Date Code\*
Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBF0201NLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MVMBF0201NLT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Chara	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS				,,,		
Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 10 μA)		V <sub>(BR)DSS</sub>	20	-	-	Vdc
Zero Gate Voltage Drain Current ( $V_{DS}$ = 16 Vdc, $V_{GS}$ = 0 Vdc) ( $V_{DS}$ = 16 Vdc, $V_{GS}$ = 0 Vdc, $V_{GS}$ = 0 Vdc, $V_{GS}$ = 0 Vdc, $V_{GS}$	: 125°C)	I <sub>DSS</sub>	_ _	_ _	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> =	± 20 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS</sub>	_	-	±100	nAdc
ON CHARACTERISTICS (Note 1)		•				
Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250 \mu Adc$ )	V <sub>GS(th)</sub>	1.0	1.7	2.4	Vdc	
$ \begin{array}{l} \text{Static Drain-to-Source On-Resistan} \\ \text{(V}_{GS} = 10 \text{ Vdc, I}_{D} = 300 \text{ mAdc)} \\ \text{(V}_{GS} = 4.5 \text{ Vdc, I}_{D} = 100 \text{ mAdc)} \end{array} $	r <sub>DS(on)</sub>	_ _	0.75 1.0	1.0 1.4	Ω	
Forward Transconductance (V <sub>DS</sub> = 1	9 <sub>F</sub> s	-	450	-	mMhos	
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>iss</sub>	-	45	_	pF
Output Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>oss</sub>	-	25	-	
Transfer Capacitance	(V <sub>DG</sub> = 5.0 V)	C <sub>rss</sub>	-	5.0	_	]
SWITCHING CHARACTERISTICS (	Note 2)					
Turn-On Delay Time		t <sub>d(on)</sub>	-	2.5	_	ns
Rise Time	(V <sub>DD</sub> = 15 Vdc, I <sub>D</sub> = 300 mAdc,	t <sub>r</sub>	-	2.5	-	
Turn-Off Delay Time	$R_L = 50 \Omega$ )	t <sub>d(off)</sub>	-	15	_	]
Fall Time		t <sub>f</sub>	-	0.8	-	]
Gate Charge (See Figure 5)	Q <sub>T</sub>	_	1400	_	pC	
SOURCE-DRAIN DIODE CHARACT	TERISTICS					
Continuous Current	I <sub>S</sub>	-	-	0.3	А	
Pulsed Current	I <sub>SM</sub>	-	-	0.75		
Forward Voltage (Note 2)	$V_{SD}$	-	0.85	-	V	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

2. Switching characteristics are independent of operating junction temperature.

### TYPICAL ELECTRICAL CHARACTERISTICS

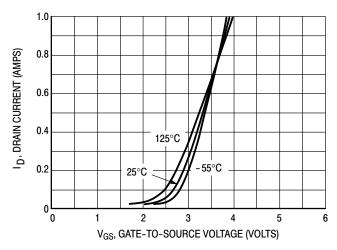


Figure 1. Transfer Characteristics

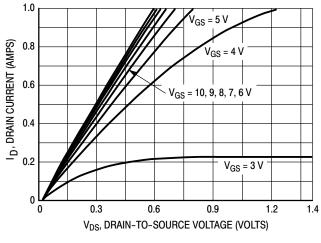


Figure 2. On-Region Characteristics

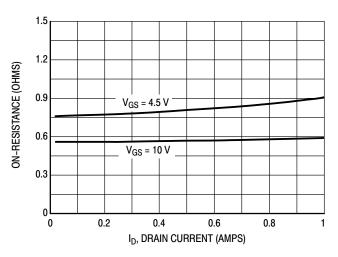


Figure 3. On-Resistance versus Drain Current

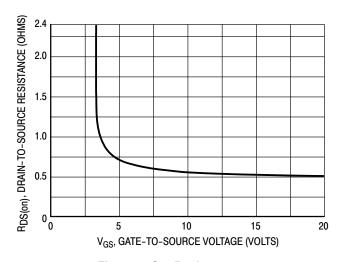


Figure 4. On–Resistance versus Gate–to–Source Voltage

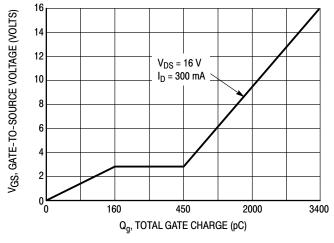


Figure 5. Gate Charge

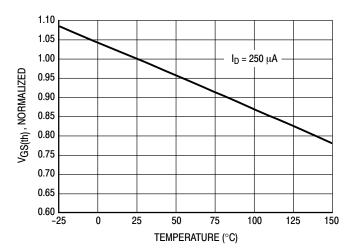


Figure 6. Threshold Voltage Variance Over Temperature

## TYPICAL ELECTRICAL CHARACTERISTICS

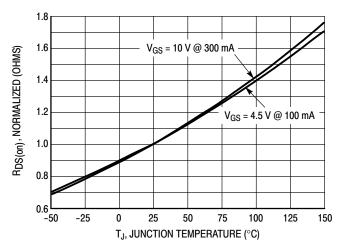


Figure 7. On–Resistance versus Junction Temperature

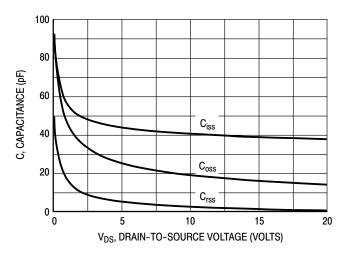


Figure 8. Capacitance

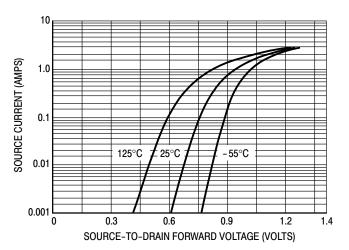


Figure 9. Source-to-Drain Forward Voltage versus Continuous Current (I<sub>S</sub>)

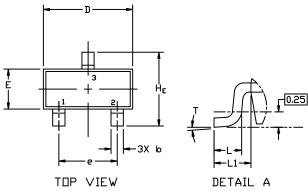




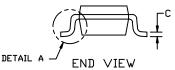
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#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10*



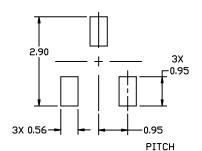


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

## **STYLES ON PAGE 2**

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## MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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